

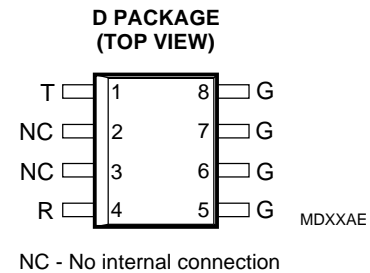
INTEGRATED SYMMETRICAL AND ASYMMETRICAL BIDIRECTIONAL OVERVOLTAGE PROTECTORS FOR LUCENT TECHNOLOGIES L7581/2/3 LINE CARD ACCESS SWITCHES

OVERVOLTAGE PROTECTION FOR LUCENT TECHNOLOGIES LCAS

- **Symmetrical and Asymmetrical Characteristics for Optimum Protection of Lucent L7581/2/3 LCAS**

TERMINAL PAIR	V _{DRM} V	V _(BO) V
T-G (SYMMETRICAL)	±105	±130
R-G (ASYMMETRICAL)	+105, -180	+130, -220

CUSTOMISED VERSIONS AVAILABLE



- **Rated for International Surge Wave Shapes**

WAVE SHAPE	STANDARD	I _{TSP} A
2/10 µs	GR-1089-CORE	175
8/20 µs	ANSI C62.41	120
10/160 µs	FCC Part 68	60
10/700 µs	ITU-T K20/21	50
10/560 µs	FCC Part 68	45
10/1000 µs	GR-1089-CORE	35

- **Ion-Implanted Breakdown Region Precise And Stable Voltage Low Voltage Overshoot Under Surge**
- **Planar Passivated Junctions Low Off-State Current < ±10 µA**
- **Small Outline Surface Mount Package - Available Ordering Options**

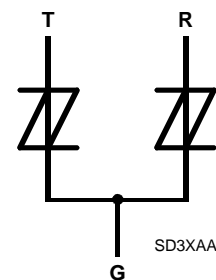
CARRIER	ORDER #
Tube	TISPL758LF3D
Taped and reeled	TISPL758LF3DR

description

The TISPL758LF3 is an integrated combination of a symmetrical bidirectional overvoltage protector and an asymmetrical bidirectional overvoltage protector. It is designed to limit the peak voltages on the line terminals of the Lucent Technologies L7581/2/3 LCAS (Line Card Access Switches). An LCAS may also be referred to as a Solid State Relay, SSR, i.e. a replacement of the conventional electro-mechanical relay.

The TISPL758LF3D voltages are chosen to give adequate LCAS protection for all switch conditions. The most potentially stressful

device symbol



Terminals T, R and G correspond to the alternative line designators of A, B and C

condition is low level power cross when the LCAS switches are closed. Under this condition, the TISPL758LF3D limits the voltage and corresponding LCAS dissipation until the LCAS thermal trip operates and opens the switches.

Under open-circuit ringing conditions, the line ring (R) conductor will have high peak voltages. For battery backed ringing, the ring conductor will have a larger peak negative voltage than positive i.e. the peak voltages are asymmetric. An overvoltage protector with a similar voltage asymmetry will give the most effective protection. On a connected line, the tip (T) conductor will have much smaller voltage levels than the open-circuit ring conductor values. Here a symmetrical voltage protector gives adequate protection.

Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. These overvoltages are initially clipped by protector breakdown clamping until the voltage rises to the breakover level, which causes the

Support from the Microelectronics Group of Lucent Technologies Inc. is gratefully acknowledged in the definition of the TISPL758LF3D voltage levels and for performing TISPL758LF3D evaluations.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.

TISPL758LF3D

INTEGRATED SYMMETRICAL AND ASYMMETRICAL BIDIRECTIONAL OVERVOLTAGE PROTECTORS FOR LUCENT TECHNOLOGIES L7581/2/3 LINE CARD ACCESS SWITCHES

JANUARY 1998 - REVISED OCTOBER 1998

device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. For negative surges, the high crowbar holding current prevents d.c. latchup with the SLIC current, as the surge current subsides. The TISPL758LF3 is guaranteed to voltage limit and withstand the listed international lightning surges in both polarities.

These protection devices are supplied in a small-outline surface mount (D) plastic package. The difference between the TISPL758LF3D and TISPL758LF3DR versions is shown in the ordering information.

absolute maximum ratings, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage	R-G terminals	V_{DRM}	-180, +105	V
	T-G terminals		-105, +105	
Non-repetitive peak on-state pulse current (see Notes 1, 2 and 3)	2/10 μs (GR-1089-CORE, 2/10 μs voltage wave shape)	I_{TSP}	175	A
	8/20 μs (ANSI C62.41, 1.2/50 μs voltage wave shape)		120	
	10/160 μs (FCC Part 68, 10/160 μs voltage wave shape)		60	
	5/200 μs (VDE 0433, 2.0 kV, 10/700 μs voltage wave shape)		50	
	0.2/310 μs (I3124, 2.0 kV, 0.5/700 μs voltage wave shape)		50	
	5/310 μs (ITU-T K20/21, 2.0 kV, 10/700 μs voltage wave shape)		50	
	5/310 μs (FTZ R12, 2.0 kV, 10/700 μs voltage wave shape)		50	
	10/560 μs (FCC Part 68, 10/560 μs voltage wave shape)		45	
	10/1000 μs (GR-1089-CORE, 10/1000 μs voltage wave shape)		35	
Non-repetitive peak on-state current (see Notes 1, 2 and 3) full sine wave	50 Hz	I_{TSM}	16	A
	60 Hz		20	
Repetitive peak on-state current, 50/60 Hz, (see Notes 2 and 3)		I_{TSM}	2x1	A
Initial rate of rise of on-state current, Exponential current ramp, Maximum ramp value < 70 A		di_T/dt	150	A/ μs
Junction temperature		T_J	-40 to +150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-40 to +150	$^\circ\text{C}$

- NOTES: 1. Above the maximum specified temperature, derate linearly to zero at 150 $^\circ\text{C}$ lead temperature.
 2. Initially the TISPL758LF3 must be in thermal equilibrium with 0 $^\circ\text{C}$ < T_J < 70 $^\circ\text{C}$.
 3. The surge may be repeated after the TISPL758LF3 returns to its initial conditions.

recommended operating conditions

			MIN	TYP	MAX	UNIT
R1	Series Resistor for GR-1089-CORE	first-level surge, operational pass (4.5.7)	20			Ω
R1	Series Resistor for FCC Part 68	10/160 non-operational pass	0			Ω
		10/160 operational pass	18			
		10/560 non-operational pass	0			
		10/560 operational pass	10			
R1	Series Resistor for ITU-T K20/21	10/700, < 2 kV, operational pass	0			Ω
		10/700, 4 kV, operational pass	40			

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PROTECTORS FOR LUCENT TECHNOLOGIES L7581/2/3 LINE CARD ACCESS SWITCHES**

JANUARY 1998 - REVISED OCTOBER 1998

electrical characteristics for the T-G and R-G terminal pairs, $T_J = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	VALUE			UNIT
		MIN	TYP	MAX	
I_{DRM} Repetitive peak off-state current	$V_D = \pm V_{\text{DRM}}$. (See Note 4)			± 10	μA
$V_{(\text{BO})}$ Breakover voltage	$dv/dt = \pm 250 \text{ V/ms}$, $R_{\text{SOURCE}} = 300 \Omega$	R-G terminals T-G terminals	-220 -130	+130 +130	V
$V_{(\text{BO})}$ Impulse breakover voltage	Rated impulse conditions with operational pass series resistor	R-G terminals T-G terminals	-240 -140	+140 +140	V
I_{H} Holding current	$di/dt = -30 \text{ mA/ms}$ $di/dt = +30 \text{ mA/ms}$		+100 -150		mA
I_{D} Off-state current	$0 < V_D < \pm 50 \text{ V}$, $T_J = 85^\circ\text{C}$			± 10	μA
C_{TG} Off-state capacitance	$f = 100 \text{ kHz}$, $V_d = 1 \text{ V rms}$ $V_{\text{TG}} = -5 \text{ V}$, (See Note 5)		18	36	pF
C_{RG} Off-state capacitance	$f = 100 \text{ kHz}$, $V_d = 1 \text{ V rms}$ $V_{\text{TG}} = -50 \text{ V}$, (See Note 5)		10	20	pF

NOTES: 4. Positive and negative values of V_{DRM} are not equal. See ratings table

5. These capacitance measurements employ a three terminal capacitance bridge incorporating a guard circuit. The third terminal is connected to the guard terminal of the bridge.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta\text{JA}}$ Junction to free air thermal resistance			160	$^\circ\text{C/W}$

PARAMETER MEASUREMENT INFORMATION

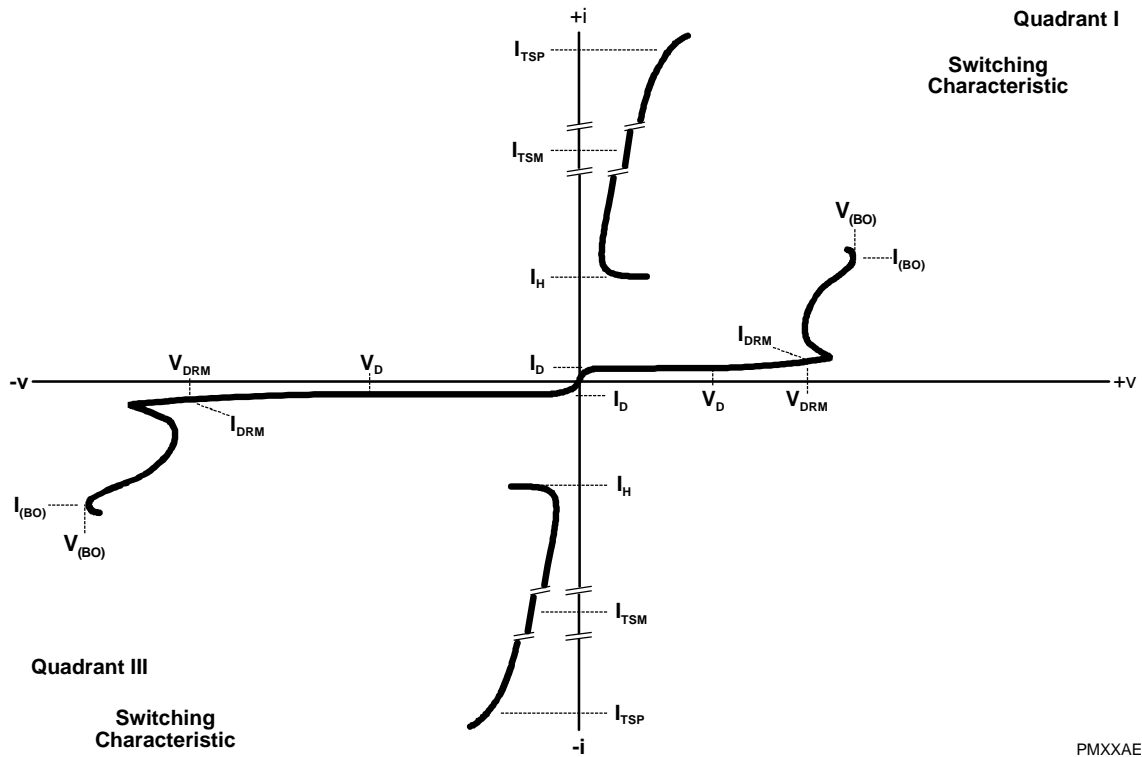


Figure 1. ASYMMETRICAL VOLTAGE-CURRENT CHARACTERISTIC FOR R-G TERMINAL PAIR

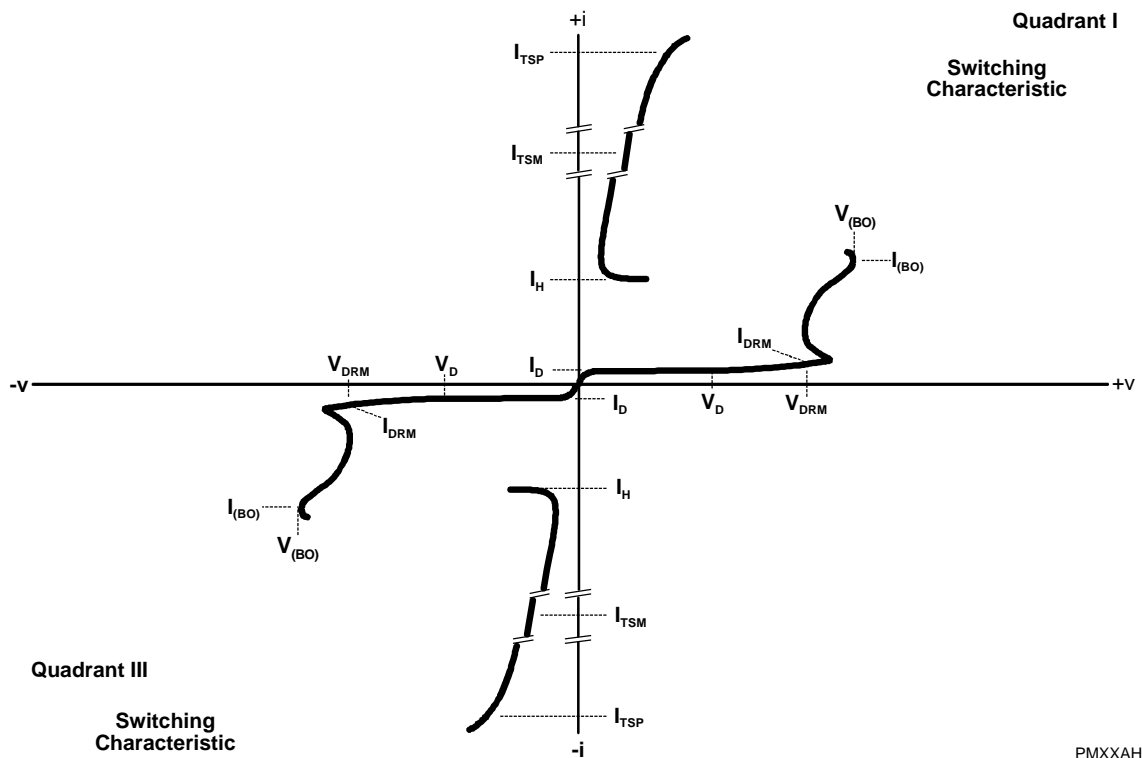


Figure 2. SYMMETRICAL VOLTAGE-CURRENT CHARACTERISTIC FOR T-G TERMINAL PAIR

PRODUCT INFORMATION

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JANUARY 1998 - REVISED OCTOBER 1998

TYPICAL CHARACTERISTICS

OFF-STATE CURRENT
vs
JUNCTION TEMPERATURE

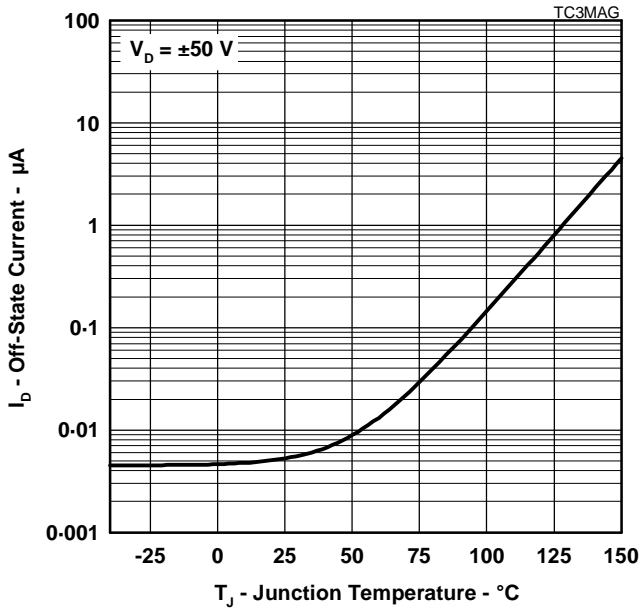


Figure 3.

NORMALISED BREAKDOWN VOLTAGES
vs
JUNCTION TEMPERATURE

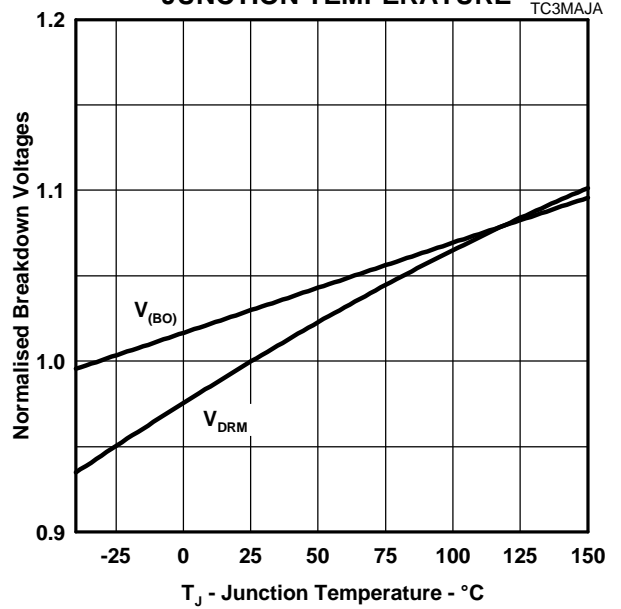


Figure 4.

NORMALISED BREAKOVER VOLTAGE
vs

RATE OF RISE OF PRINCIPLE CURRENT

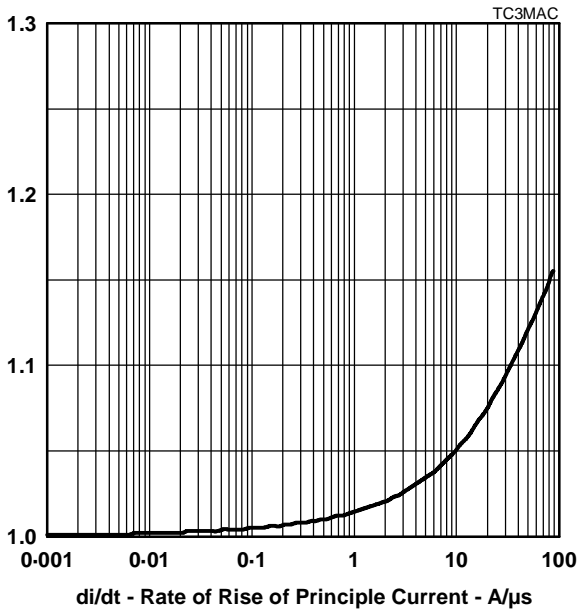


Figure 5.

NORMALISED HOLDING CURRENT
vs

JUNCTION TEMPERATURE

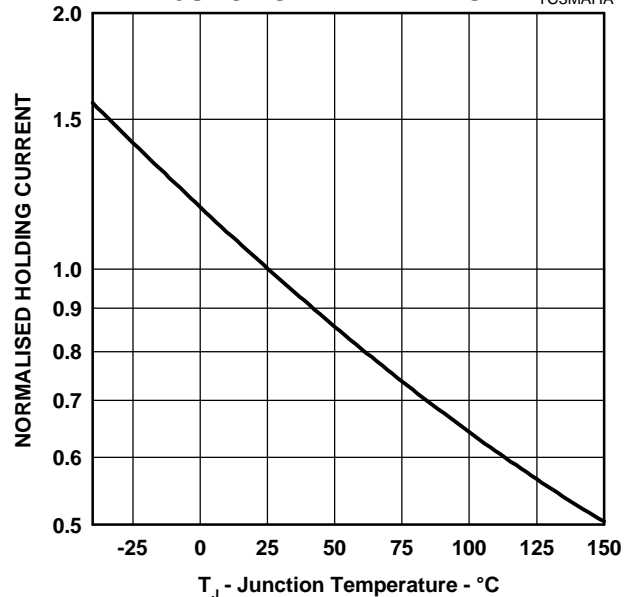


Figure 6.

APPLICATIONS INFORMATION

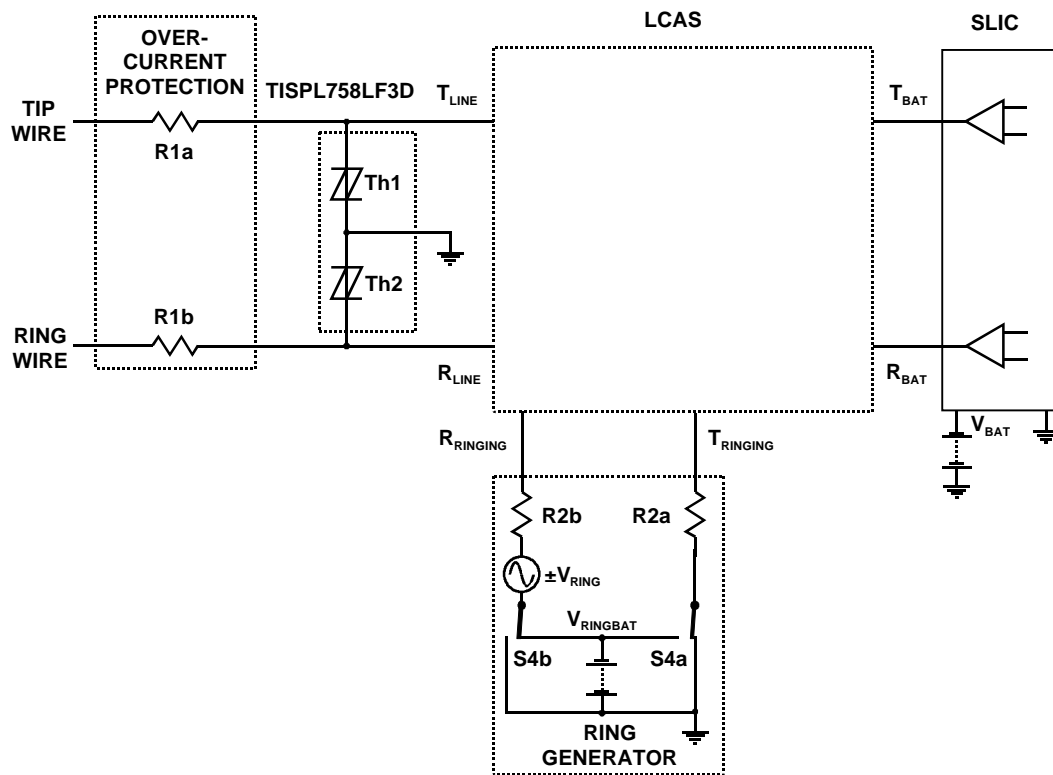


Figure 7. LCAS PROTECTION WITH A TISPL758LF3D

TISPL758LF3D
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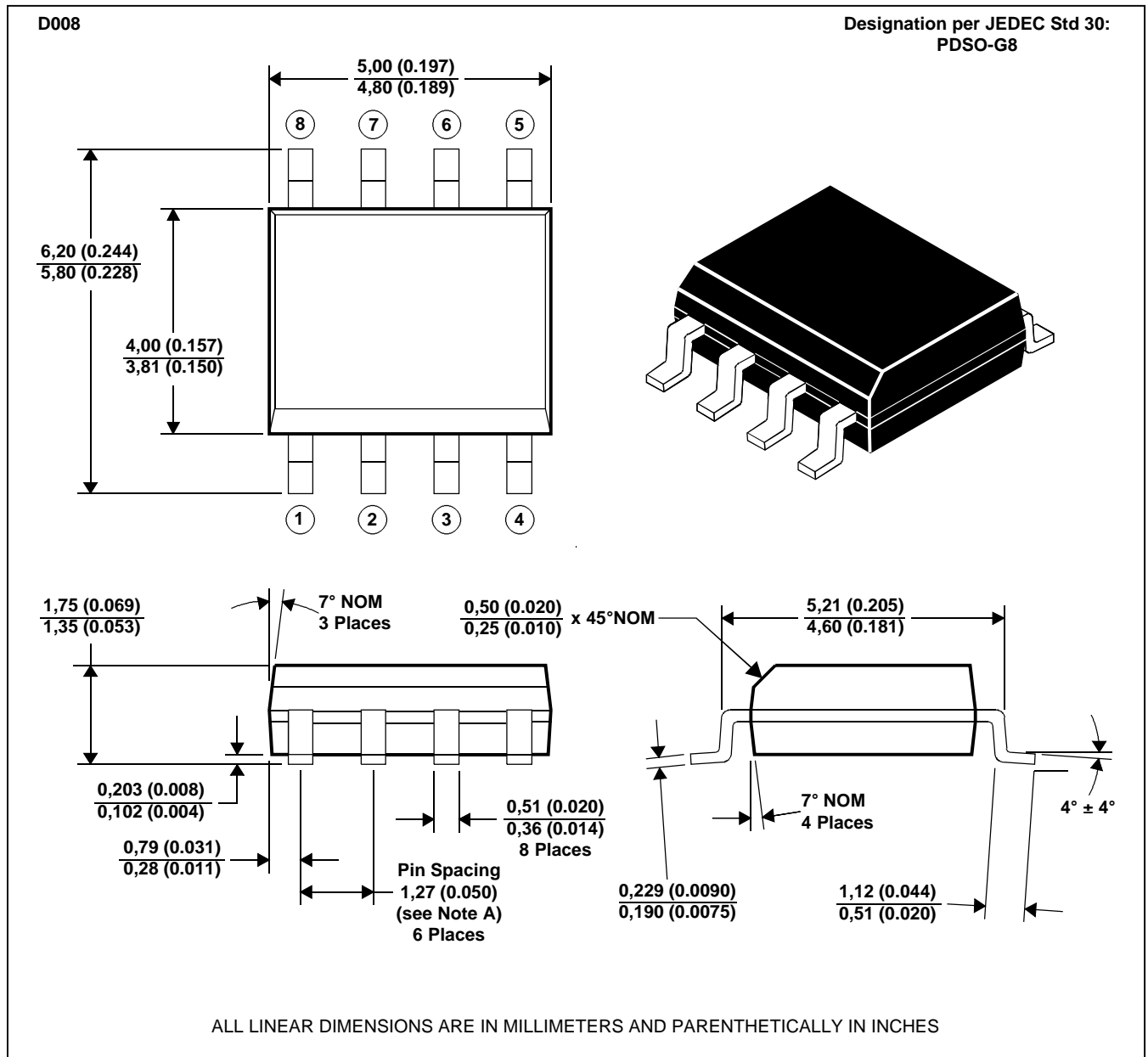
JANUARY 1998 - REVISED OCTOBER 1998

MECHANICAL DATA

D008

plastic small-outline package

This small-outline package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



- NOTES: A. Leads are within 0,25 (0.010) radius of true position at maximum material condition.
 B. Body dimensions do not include mold flash or protrusion.
 C. Mold flash or protrusion shall not exceed 0,15 (0.006).
 D. Lead tips to be planar within ±0,051 (0.002).

MDXXAA

PRODUCT INFORMATION



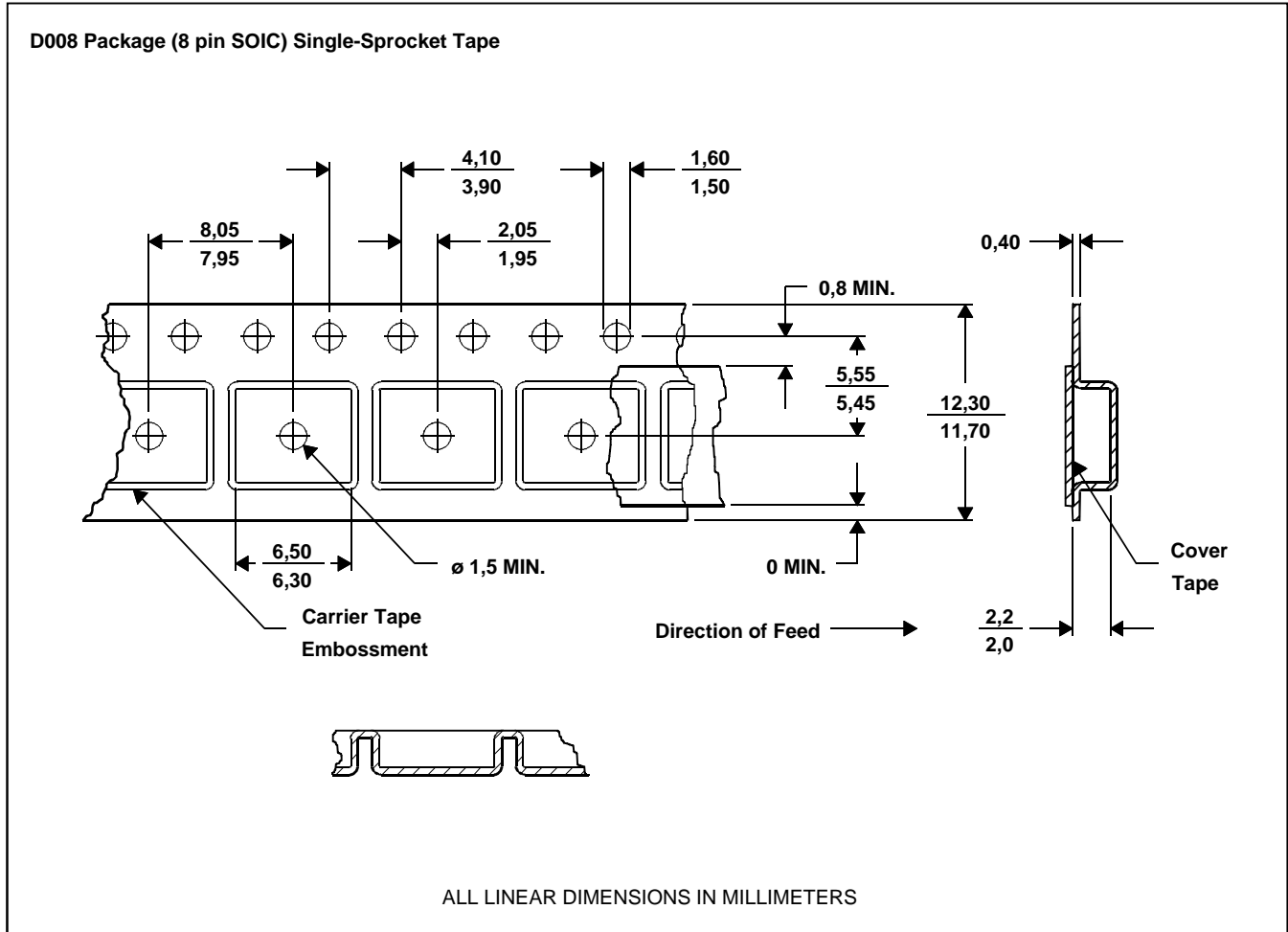
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JANUARY 1998 - REVISED OCTOBER 1998

MECHANICAL DATA

D008

tape dimensions



NOTES: A. Taped devices are supplied on a reel of the following dimensions:-

MDXXAT

Reel diameter: 330 +0,0/-4,0 mm
 Reel hub diameter: 100 ±2,0 mm
 Reel axial hole: 13,0 ±0,2 mm

B. 2500 devices are on a reel.

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JANUARY 1998 - REVISED OCTOBER 1998

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